

Serial No. 10/035,257Attorney Docket No. 262/014**LISTING OF THE CLAIMS:**

1. (Previously Presented) A method of fabricating a semiconductor device having a recess region in an insulation layer on a silicon substrate, the method comprising the steps of:

depositing a barrier metal on the whole surface of the insulation layer including the substrate surface in the recess region;

depositing selectively an anti-nucleation layer on the barrier metal except in the recess region;

depositing a CVD-Al layer on the barrier metal in the recess region;

depositing a metal or a metal alloy for inhibiting aluminum migration on the anti-nucleation layer and the barrier metal except in the recess region; and

depositing a PVD-Al layer and reflowing the PVD-Al layer.
2. (Original) The fabrication method of claim 1, wherein the metal or the metal alloy inhibiting aluminum migration is one of Ti, TiN, Ti/TiN, Ta, TaN and Ta/TaN.
3. (Original) The fabrication method of claim 1, wherein a deposition thickness of the metal or the metal alloy inhibiting aluminum migration is less than 100 Å.